

Abstract of the Disclosure

There is described a semiconductor device which prevents a short circuit between a wiring layer formed in interlayer insulating films and vertical conductor plugs formed in the vicinity of the wiring layer, and a method of manufacturing the semiconductor device.

- 5 The semiconductor device includes a first interlayer insulating film smoothly formed on a semiconductor substrate, conductor plugs which are formed by filling openings formed in the first interlayer insulating film so as to be level with the surface of the first interlayer insulating film, a second interlayer insulating film formed on the surface of the first interlayer insulating film and of the conductor plugs, a wiring pattern formed on the
- 10 second interlayer insulating film, a third interlayer insulating film formed on the surface of the second interlayer insulating film so as to cover the wiring pattern, and an interconnect conductor formed so as to be electrically connected to the conductor plugs by filling the openings penetrating the second and third interlayer insulating films.